

We Claim:

1. A quasi-vertical semiconductor component, comprising:

a surface;

a semiconductor substrate;

a well;

at least two inner cells disposed in said well and having a substantially similar operating point, thereby compensating for differences between said inner cells;

a buried layer disposed between said well and said semiconductor substrate; and

a sinker zone connecting said buried layer to said surface of the semiconductor component.

2. The semiconductor component according to claim 1, wherein said inner cells have a given width and a given radius of curvature, and the substantially similar operating point of said inner cells is set by varying at least one of said given width, said given radius of curvature and a grid configuration of said inner cells.

3. The semiconductor component according to claim 2, wherein said inner cells have body zones with a given width and a given radius of curvature, and that at least one of said given width of said body zones, said given radius of curvature of said body zones, and a grid configuration of said body zones of said inner cells is varied.

4. The semiconductor component according to claim 3, wherein said body zones are one of wider and have a larger radius of curvature in a vicinity of said sinker zone than at a distance from said sinker zone.

5. The semiconductor component according to claim 3, wherein said grid configuration of said inner cells has a larger spacing distance at a distance from said sinker zone than in a vicinity of said sinker zone.

6. The semiconductor component according to claim 2, further comprising doped regions disposed in said well, a variation of at least one of said given width, said given radius of curvature and said grid configuration of said inner zones is effected by said doped regions.

7. The semiconductor component according to claim 6, wherein said doped regions are introduced by high-energy ion implantation.

8. The semiconductor component according to claim 7, wherein said doped regions lie between said well and said body zone of said inner cells.

9. The semiconductor component according to claim 1, wherein said well has an edge region and said sinker zone is disposed at said edge region.